

(19)  
(12)

(KR)  
(A)

(51) 。 Int. Cl.<sup>7</sup>  
H05B 33/10

(11)  
(43)

10-2004-0067929  
2004 07 30

(21) 10-2004-0003219  
(22) 2004 01 16

(30) JP-P-2003-00011451 2003 01 20 (JP)

(71) 가 가 2 4-1

(72) 가 3 3-5 가 가  
가 3 3-5 가 가

(74)

:

(54)

EL , 가  
, EL , EL  
1 (3) , 1 (3)  
, 1 (3) 2 (5) , 2 (4) 1 (3) , 1 (3)  
, 1 (3) 2 (5) . 2 (5)

1

1 1 ,

2 EL ,

3 ,

4 3(a) ,  
 5 ,  
 6 ,  
 7 EL ,  
 8 ,  
 9 5 ,  
 10 .

1 : 2 : 1  
 3 : 1 4 : 2  
 5 : 2 6 :  
 7 : TFT 8 :  
 9 : ITO 10 :  
 11 : 12 :  
 13 : 14 : ITO  
 15 : 17 :  
 20 : 21R :  
 21G : 21B :

, ( , EL ) , EL  
 , EL  
 , (100)  
 ( , EL 1 ) . ,  
 , (100) ( ) ( ,  
 2 ) . ,

, EL , 10  
가 , , .

[ 1] 2001-185350 ( 7 , 1)

[ 2] 4-236758 ( 4 , 1)

1 ), , EL 가 ( ± 5  
가 , 가

, 2 (100) , 10 가 ( ,  
가 ,

, EL , , EL , 가  
EL , EL ,

, 1 , 1 , 2 1 1  
2 , 1 2 , 2 1  
1 , 2 가, 1 1 가  
1 , 2 가 , 1 가  
가 , 1 가  
가 , 1 가

, 1 2 가

, 1 2 가 ,

, 1 2 (111)

2 , 1 2 (111) , 1





(3) (1) , 1 (2) . . . , 1

2

3 1 (1) , (110)  
 (17) , (SiO<sub>2</sub>) (17) (1) , (1) (3(a)).  
 , CVD(Chemichal Vapor Deposition)

2 , (1) 가 1.7 × 10<sup>18</sup> atm/cm<sup>3</sup>  
 가 500 800 , (17) (1) , (1)

4 3(a) (17) . 800  
 가 , 1100 , 가 1100 (17)  
 , 1100 (17)

(1) 500 800 가 3 /  
 , 가 ,

, CVD (17) 500 (17) , 500 8  
 00 3 / ,

(1) 가 1.7 × 10<sup>18</sup> atm/cm<sup>3</sup>  
 3 / , (1) 가 500 800  
 가 1.7 × 10<sup>18</sup> atm/cm<sup>3</sup>

1 , 3(a) (17) (1) 2 1 (3)  
 4) (2) , (5) 2 (

(1) 5 , 5 (1) 6 5 6  
 , 5 6 J, K (111) .

(1) EL (12) (

3(b)). 20) 1 (

2 , 3(b) (1) , 1 (2)  
 (4) ( 3(c)). (111)  
 가 , EL 가 , 가

3(c) (1) (17) ,  
 ( 3(d)).

2 가 , ,  
 1 가 (1) 가 500 800 , 3 / 가 1.7  
 × 10<sup>18</sup> atm/cm<sup>3</sup> , (1) , 가 1.7  
 가 .

3

1, 2, 3, EL

3, EL

7 EL, TFT, TFT(Thin Film Transistor), EL, EL, TFT

ON·OFF, EL, TFT

TFT, 가 20 EL, TFT, 가 60, 가

1, 1 (2)가 가, EL

3, 1 가 1 가, TFT

4

8 EL, 2 EL

(6) EL, (1), 8 (7), (1)

(8), ITO (9) (10) (1)(6), TFT (2)가

(2) (1) 8 (1) 1 (2) 3 (21R),

(21G), (21B) (6) (1)

10 (6), 2 (2) (6) (1) ( )

가 (6) (1)

1 (1) (2)가 가 (6) (1)

EL

가 가, 가 10

가 가 2 (5)가 1 (3) 2 1 (5)

1 (3)

(6) (12) (1) 2 (5) 가

4 (6) , 가

가 (5) 1 (2) (12) , (6) (1) (1)) 2  
5

9 5 9(a) 9(b)

EL EL

(57)

1. 1 (brace) ,

2 1 1 2

1 2

2. 1

1 2 가

3. 2

4. 3

1 2 (111)

5. 3

(110) 1 (110) (111)  
 1 (110) (111)  
 2

6. 5

가  $1.7 \times 10^{18} \text{ atm/cm}^3$

7.

5 6

,

1 2 1 2

,

1 2

8.

7

가 500 800

500 가

3 /

9.

8

10.

5 6

(electroluminescence laye

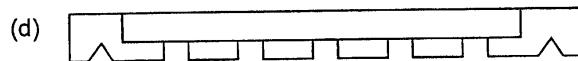
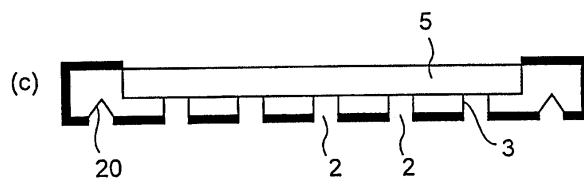
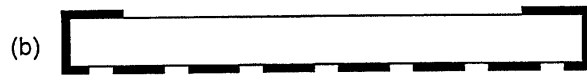
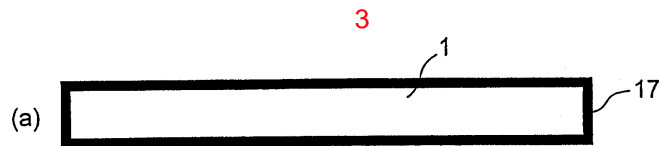
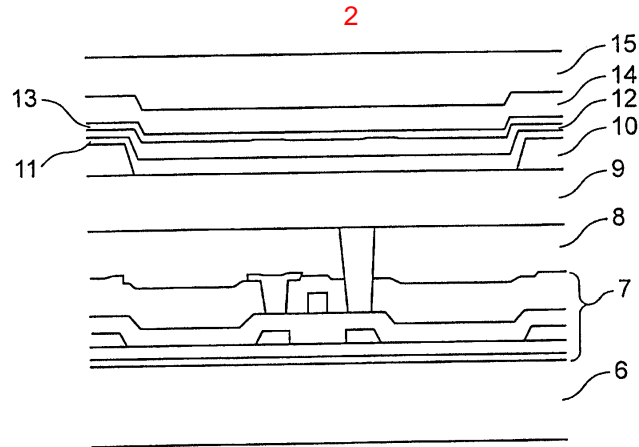
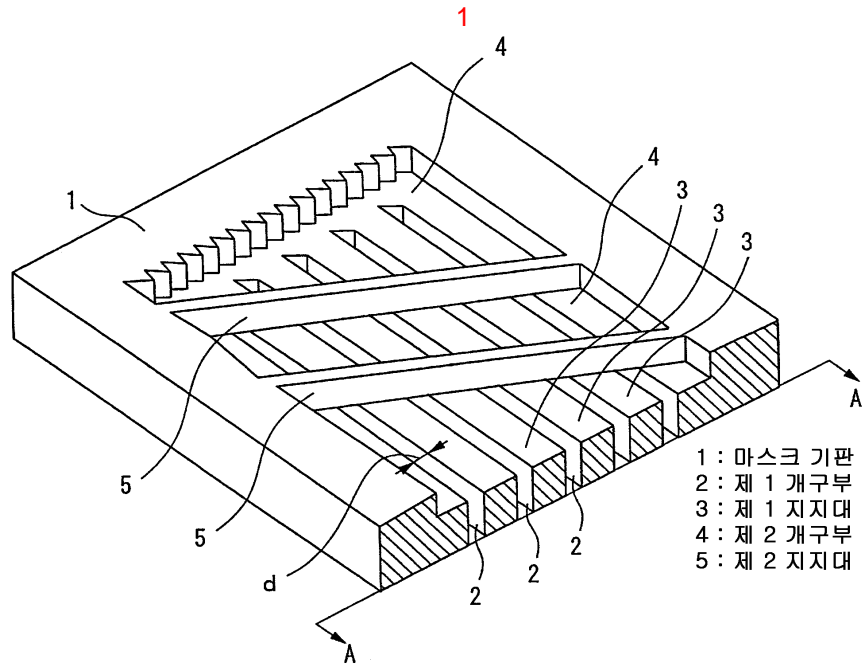
r)

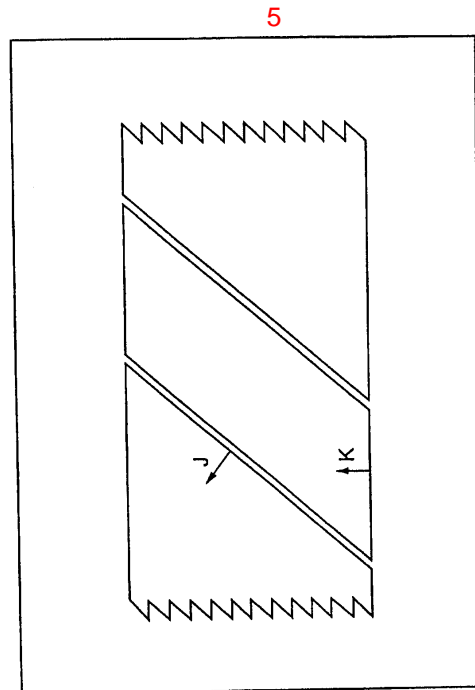
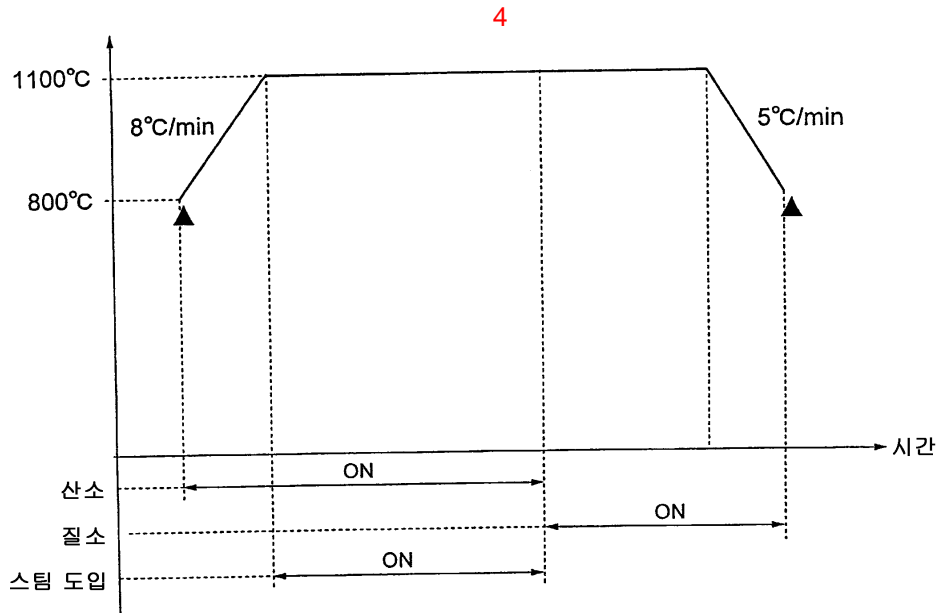
11.

5 6

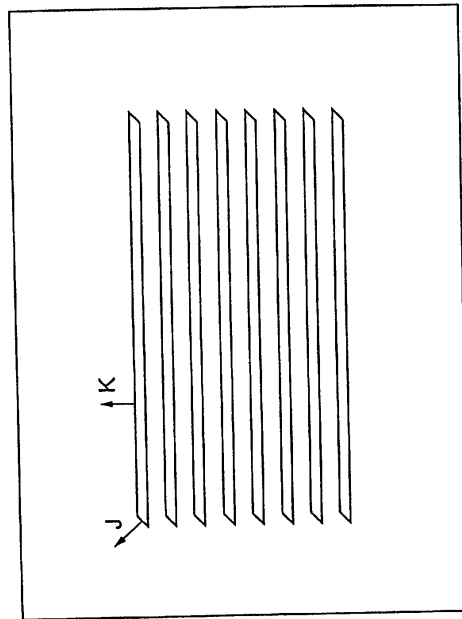
12.

10



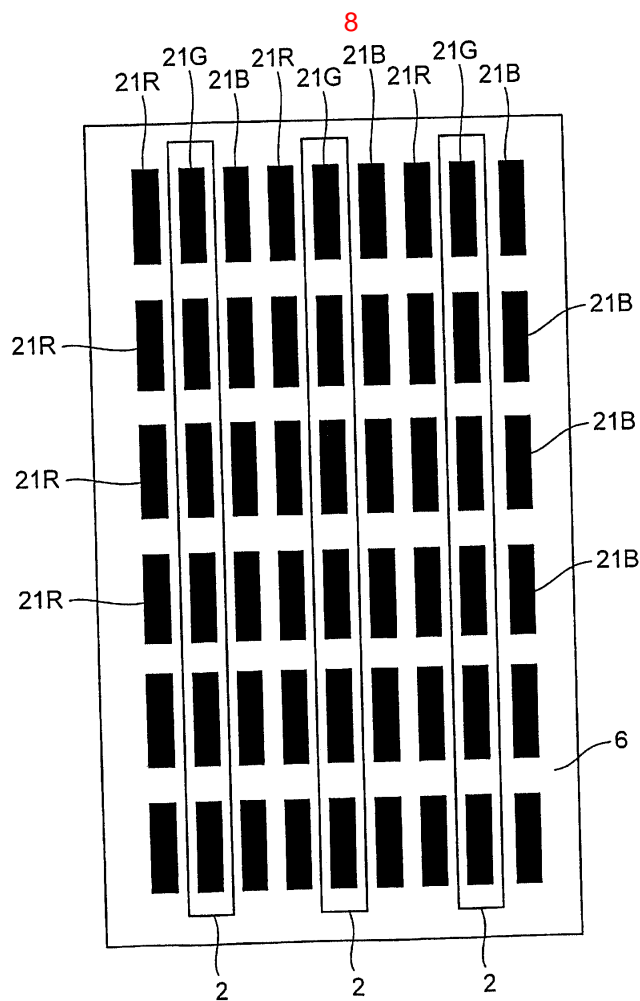


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7

배열 명칭	화소 배열 약도	TFT 배선 난이도	화상	문자
세로 스트라이프	A simplified diagram of the vertical stripe pattern, showing three vertical black bars. A dashed rectangular box encloses the top two bars, and another dashed rectangular box encloses the bottom two bars.	단순	○	○
델타 배열	A simplified diagram of a delta pixel arrangement, showing three black squares. Two squares are at the top, and one is centered below them. A dashed rectangular box encloses the top two squares.	복잡	○	△
정방 배열	A simplified diagram of a square pixel arrangement, showing four black squares in a 2x2 grid. A dashed rectangular box encloses all four squares.	복잡	○	○

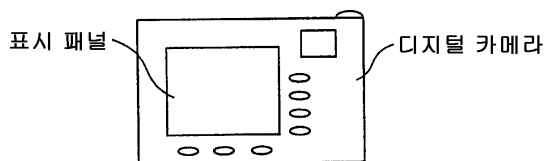


(a)

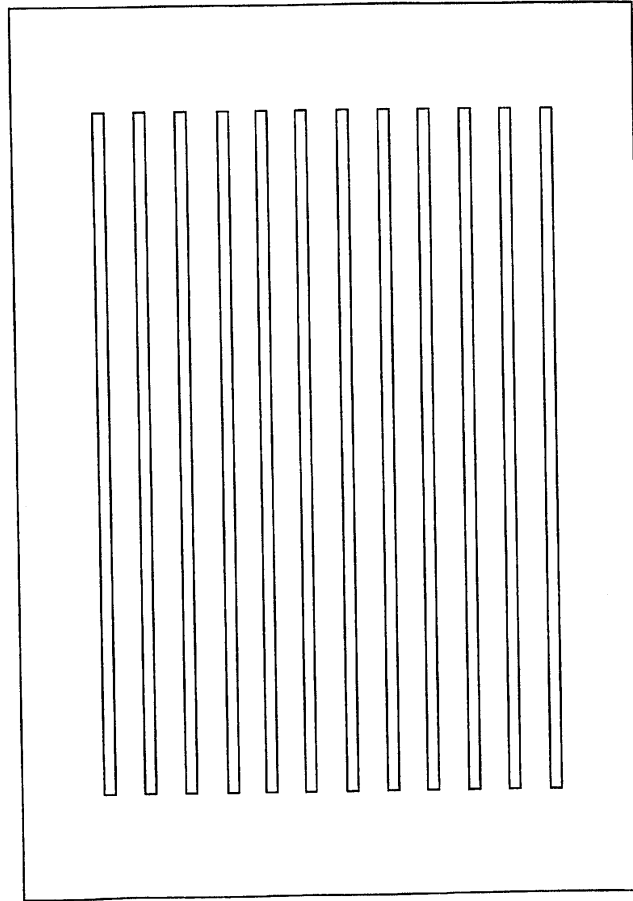
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(b)



10



专利名称(译)	用于成膜的精密掩模及其制造方法，电致发光显示装置及其制造方法，电子装置		
公开(公告)号	<a href="#">KR1020040067929A</a>	公开(公告)日	2004-07-30
申请号	KR1020040003219	申请日	2004-01-16
[标]申请(专利权)人(译)	精工爱普生株式会社		
申请(专利权)人(译)	精工爱普生株式会社		
当前申请(专利权)人(译)	精工爱普生株式会社		
[标]发明人	YOTSUYA SHINICHI 요츠야신이치 KUWAHARA TAKAYUKI 구와하라다카유키		
发明人	요츠야신이치 구와하라다카유키		
IPC分类号	H01L51/50 C23C14/24 C23C14/04 C23C14/12 H05B33/10		
CPC分类号	C23C14/12 H01L51/0011 H01L51/001 C23C14/042 Y10T428/24273		
代理人(译)	KIM, CHANG SE		
优先权	2003011451 2003-01-20 JP		
其他公开文献	KR100645606B1		
外部链接	<a href="#">Espacenet</a>		

摘要(译)

在包括有机EL显示装置等的发光层的沉积中，促进了玻璃板组的位置对准。此外，提供了用于沉积的精密掩模，其中强度足够并且形成正确的沉积图案。此外，提供了一种电子装置，其具有简单且真实地制造用于该沉积的精密掩模的方法，以及有机EL显示装置及其制造方法，以及有机EL显示装置。并行地，它具有预定的间隙并且被布置。一个形成多个第二开口(4)，其形成第一支撑件(3)的上部，形成第一支撑件(3)或多个第二支撑架(5)，多个第一开口(2)。第一支撑件(3)和第二支撑架(5)的交叉部分连接。

